

Wireless Components

ASK/FSK Transmitter 868/433 MHz TDK 5100 Version 1.1

Specification May 2012

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fail, it is reasonable to assume that the health of the user may be en

Product Info

1 Product Description

Contents of this Chapter

1.1 Overview

The TDK 5100 is a single chip ASK/FSK transmitter for the frequency bands 433-435 MHz and 868-870 MHz. The IC offers a high level of integration and needs only a few external components. The device contains a fully integrated PLL synthesizer and a high efficiency power amplifier to drive a loop antenna. A special circuit design and an unique power amplifier design are used to save current consumption and therefore to save battery life. Additional features like a power down mode, a low power detect, a selectable crystal oscillator frequency and a divided clock output are implemented. The IC can be used for both ASK and FSK modulation.

1.2 Applications

- Keyless entry systems
- Remote control systems
- Alarm systems
- Communication systems

1.3 Features

- fully integrated frequency synthesizer
- VCO without external components
- ASK and FSK modulation
- switchable frequency range 433-435 MHz / 868-870 MHz
- high efficiency power amplifier (typically 5 dBm / 2 dBm)
- low supply current (typically 7 mA)
- voltage supply range 2.1 4 V
- temperature range -40°C ... 125°C
- power down mode
- low voltage sensor
- selectable crystal oscillator 6.78 MHz / 13.56 MHz
- $-$ programmable divided clock output for μ C
- low external component count

1.4 Package Outlines

1) Does not include plastic or metal protrusion of 0.15 max. per side 2) Does not include dambar protrusion

2 Functional Description

Contents of this Chapter

2.1 Pin Configuration

Pin_config.wmf

Figure 2-1 IC Pin Configuration

Table 2-1		
Pin No.	Symbol	Function
1	PDWN	Power Down Mode Control
$\overline{2}$	LPD	Low Power Detect Output
3	VS	Voltage Supply
4	LF	Loop Filter
5	GND	Ground
6	ASKDTA	Amplitude Shift Keying Data Input
$\overline{7}$	FSKDTA	Frequency Shift Keying Data Input
8	CLKOUT	Clock Driver Output
9	CLKDIV	Clock Divider Control (847.5 kHz or 3.34 MHz)
10	COSC	Crystal Oscillator Input
11	FSKOUT	Frequency Shift Keying Switch Output
12	FSKGND	Frequency Shift Keying Ground
13	PAGND	Power Amplifier Ground
14	PAOUT	Power Amplifier Output
15	FSEL	Frequency Range Selection (433 or 868 MHz)
16	CSEL	Crystal Frequency Selection (6.78 or 13.56 MHz)

2.2 Pin Definitions and Functions

*) Indicated voltages and currents apply for PLL Enable Mode and Transmit Mode. In Power Down Mode, the values are zero or high-ohmic.

2.3 Functional Block diagram

Figure 2-2 Functional Block diagram

Block_diagram.wmf

2.4 Functional Blocks

2.4.1 PLL Synthesizer

The Phase Locked Loop synthesizer consists of a Voltage Controlled Oscillator (VCO), an asynchronous divider chain, a phase detector, a charge pump and a loop filter. It is fully implemented on chip. The tuning circuit of the VCO consisting of spiral inductors and varactor diodes is on chip, too. Therefore no additional external components are necessary. The nominal center frequency of the VCO is 869 MHz. The oscillator signal is fed both, to the synthesizer divider chain and to the power amplifier. The overall division ratio of the asynchronous divider chain is 128 in case of a 6.78 MHz crystal or 64 in case of a 13.56 MHz crystal and can be selected via CSEL (pin 16). The phase detector is a Type IV PD with charge pump. The passive loop filter is realized on chip.

2.4.2 Crystal Oscillator

The crystal oscillator operates either at 6.78 MHz or at 13.56 MHz.

The reference frequency can be chosen by the signal at CSEL (pin 16).

For both quartz frequency options, 847.5 kHz or 3.39 MHz are available as output frequencies of the clock output CLKOUT (pin 8) to drive the clock input of a micro controller.

The frequency at CLKOUT (pin 8) is controlled by the signal at CLKDIV (pin 9)

Ü) Open: Pin open

To achieve FSK transmission, the oscillator frequency can be detuned by a fixed amount by switching an external capacitor via FSKOUT (pin 11).

The condition of the switch is controlled by the signal at FSKDTA (pin 7).

2.4.3 Power Amplifier

In case of operation in the 868-870 MHz band, the power amplifier is fed directly from the voltage controlled oscillator. In case of operation in the 433-435 MHz band, the VCO frequency is divided by 2. This is controlled by FSEL (pin 15) as described in the table below.

Ü) Open: Pin open

The Power Amplifier can be switched on and off by the signal at ASKDTA (pin 6).

á) High: Voltage at pin > 1.5 V

The Power Amplifier has an Open Collector output at PAOUT (pin 14) and requires an external pull-up coil to provide bias. The coil is part of the tuning and matching LC circuitry to get best performance with the external loop antenna. To achieve the best power amplifier efficiency, the high frequency voltage swing at PAOUT (pin 14) should be twice the supply voltage.

The power amplifier has its own ground pin PAGND (pin 13) in order to reduce the amount of coupling to the other circuits.

2.4.4 Low Power Detect

The supply voltage is sensed by a low power detector. When the supply voltage drops below 2.15 V, the output LPD (pin 2) switches to the low-state. To minimize the external component count, an internal pull-up current of 40 µA gives the output a high-state at supply voltages above 2.15 V.

The output LPD (pin 2) can either be connected to ASKDTA (pin 6) to switch off the PA as soon as the supply voltage drops below 2.15 V or it can be used to inform a micro-controller to stop the transmission after the current data packet.

2.4.5 Power Modes

The IC provides three power modes, the POWER DOWN MODE, the PLL ENABLE MODE and the TRANSMIT MODE.

2.4.5.1 Power Down Mode

In the POWER DOWN MODE the complete chip is switched off.

The current consumption is typically 0.3 nA at 3 V 25°C.

This current doubles every 8°C. The values for higher temperatures are typically 14 nA at 85°C and typically 600 nA at 125°C.

2.4.5.2 PLL Enable Mode

In the PLL ENABLE MODE the PLL is switched on but the power amplifier is turned off to avoid undesired power radiation during the time the PLL needs to settle. The turn on time of the PLL is determined mainly by the turn on time of the crystal oscillator and is less than 1 msec when the specified crystal is used.

The current consumption is typically 3.5 mA.

2.4.5.3 Transmit Mode

In the TRANSMIT MODE the PLL is switched on and the power amplifier is turned on too.

The current consumption of the IC is typically 7 mA when using a proper transforming network at PAOUT, see Figure 3-1.

2.4.5.4 Power mode control

The bias circuitry is powered up via a voltage $V > 1.5 V$ at the pin PDWN (pin 1). When the bias circuitry is powered up, the pins ASKDTA and FSKDTA are pulled up internally.

Forcing the voltage at the pins low overrides the internally set state.

Alternatively, if the voltage at ASKDTA or FSKDTA is forced high externally, the PDWN pin is pulled up internally via a current source. In this case, it is not necessary to connect the PDWN pin, it is recommended to leave it open.

The principle schematic of the power mode control circuitry is shown in Figure 3-5.

Figure 2-5 Power mode control circuitry

Table 3-8 provides a listing of how to get into the different power modes

Other combinations of the control pins PDWN, FSKDTA and ASKDTA are not recommended.

2.4.6 Recommended timing diagrams for ASK- and FSK-Modulation

ASK Modulation using FSKDTA and ASKDTA, PDWN not connected

Figure 2-6 ASK Modulation

FSK Modulation using FSKDTA and ASKDTA, PDWN not connected

Figure 2-7 FSK Modulation

FSK_mod.wmf

Alternative ASK Modulation, FSKDTA not connected.

Figure 2-8 Alternative ASK Modulation

Contents of this Chapter

3.1 50 Ohm-Output Testboard Schematic

50ohm_test_v5.wmf

Figure 3-1 50 Ω - output testboard schematic

3.2 50 Ohm-Output Testboard Layout

Oben (3.00 09/14/99) tda5100_v5.tc)

Figure 3-2 Top Side of TDK 5100-Testboard with 50 Ω - Output

Unten (3.00 09/14/99 tda5100_v5.tc) Figure 3-3 Bottom Side of TDK 5100-Testboard with 50 Ω - Output

3.3 Bill of material (50 Ohm-Output Testboard)

3.4 50 Ohm-Output Testboard: Measurement results

Note the specified operating range: 2.1 V to 4.0 V and -40°C to +125°C.

pout_over_temp_434.wmf

Figure 3-4 Output power over temperature of the 50 Ω - testboard with TDK 5100 at 434 MHz

Is_over_temp_434.wmf

Figure 3-5 Supply current over temperature of the 50 Ω - testboard with TDK 5100 at 434 MHz

Note the specified operating range: 2.1 V to 4.0 V and -40°C to +125°C.

pout_over_temp_868.wmf

Figure 3-6 Output power over temperature of the 50 Ω - testboard with TDK 5100 at 868 MHz

is_over_temp_868.wmf

Figure 3-7 Supply current over temperature of the 50 Ω - testboard with TDK 5100 at 868 MHz

3.5 Application Hints on the Crystal Oscillator

1. Application Hints on the crystal oscillator

The crystal oscillator achieves a turn on time less than 1 msec when the specified crystal is used. To achieve this, a NIC oscillator type is implemented in the TDK 5100. The input impedance of this oscillator is a negative resistance in series to an inductance. Therefore the load capacitance of the crystal CL (specified by the crystal supplier) is transformed to the capacitance Cv.

$$
Cv = \frac{1}{\frac{1}{CL} + \omega^2 L}
$$
 Formula 1)

- CL: crystal load capacitance for nominal frequency
- ω: angular frequency
- L: inductance of the crystal oscillator

Example for the ASK-Mode:

Referring to the application circuit, in ASK-Mode the capacitance C7 is replaced by a short to ground. Assume a crystal frequency of 13.56 MHz and a crystal load capacitance of CL = 20 pF. The inductance L at 13.5 MHz is about 4.6 mH. Therefore C6 is calculated to 12 pF.

$$
Cv = \frac{1}{\frac{1}{CL} + \omega^2 L} = C6
$$

Example for the FSK-Mode:

FSK modulation is achieved by switching the load capacitance of the crystal as shown below.

The frequency deviation of the crystal oscillator is multiplied with the divider factor N of the Phase Locked Loop to the output of the power amplifier. In case of small frequency deviations (up to +/- 1000 ppm), the two desired load capacitances can be calculated with the formula below.

$$
CL \pm C0 \frac{\Delta f}{N * f1} (1 + \frac{2(C0 + CL)}{C1})
$$

$$
CL \pm \frac{\Delta f}{N * f1} (1 + \frac{2(C0 + CL)}{C1})
$$

- C_1 : : crystal load capacitance for nominal frequency
- C_0 :
f: : shunt capacitance of the crystal
- frequency
- ω: $ω = 2πf$: angular frequency
- N: division ratio of the PLL
df: peak frequency deviation
- peak frequency deviation

Because of the inductive part of the TDK 5100, these values must be corrected by Formula 1). The value of Cv± can be calculated.

$$
Cv\pm = \frac{1}{\frac{1}{CL\pm} + \omega^2 L}
$$

If the FSK switch is closed, Cv is equal to Cv1 (C6 in the application diagram). If the FSK switch is open, Cv2 (C7 in the application diagram) can be calculated.

$$
Cv2 = C7 = \frac{Csw * Cv1 - (Cv+) * (Cv1 + Csw)}{(Cv+) - Cv1}
$$

- Csw: parallel capacitance of the FSK switch (3 pF incl. layout parasitics)
- Remark: These calculations are only approximations. The necessary values depend on the layout also and must be adapted for the specific application board.

3.6 Design Hints on the Clock Output (CLKOUT)

The CLKOUT pin is an open collector output. An external pull up resistor (RL) should be connected between this pin and the positive supply voltage. The value of RL is depending on the clock frequency and the load capacitance CLD (PCB board plus input capacitance of the microcontroller). RL can be calculated to:

$$
RL = \frac{1}{fCLKOUT*8*CLD}
$$

Remark: To achieve a low current consumption and a low spurious radiation, the largest possible RL should be chosen.

Even harmonics of the signal at CLKOUT can interact with the crystal oscillator input COSC preventing the start-up of oscillation. Care must be taken in layout by sufficient separation of the signal lines to ensure sufficiently small coupling.

3.7 Application Hints on the Power-Amplifier

The power amplifier operates in a high efficient class C mode. This mode is characterized by a pulsed operation of the power amplifier transistor at a current flow angle of θ < π . A frequency selective network at the amplifier output passes the fundamental frequency component of the pulse spectrum of the collector current to the load. The load and its resonance transformation to the collector of the power amplifier can be generalized by the equivalent circuit of [Figure 3-8.](#page-28-1) The tank circuit L//C//RL in parallel to the output impedance of the transistor should be in resonance at the operating frequency of the transmitter.

Equivalent_power_wmf.

Figure 3-8 Equivalent power amplifier tank circuit

The optimum load at the collector of the power amplifier for "critical" operation under idealized conditions at resonance is:

$$
R_{LC} = \frac{V_s^2}{2 * P_o}
$$

The theoretical value of R_{LC} for an RF output power of P_0 = 5 dBm (3.16 mW) is:

$$
R_{LC} = \frac{3^2}{2 * 0.00316} = 1423 \,\Omega
$$

ìCriticalî operation is characterized by the RF peak voltage swing at the collector of the PA transistor to just reach the supply voltage $V_{\rm S}$.

The high degree of efficiency under "critical" operating conditions can be explained by the low power losses at the transistor. During the conducting phase of the transistor, its collector voltage is very small. This way the power loss of the transistor, equal to $i_C^*u_{CE}$, is minimized. This is particularly true for small current flow angles of $\theta < \pi$.

In practice the RF-saturation voltage of the PA transistor and other parasitics reduce the "critical" R_{LC} .

The output power P_o is reduced by operating in an "overcritical" mode characterised by R_L > R_{LC} .

The power efficiency (and the bandwidth) increase when operating at a slightly higher R_{L} , as shown in [Figure 3-9.](#page-29-0)

The collector efficiency E is defined as

$$
E = \frac{P_o}{V_s I_c}
$$

The diagram of [Figure 3-9](#page-29-0) was measured directly at the PA-output at $V_S = 3 V$. Losses in the matching circuitry decrease the output power by about 1.5 dB. As can be seen from the diagram, 700 Ω is the optimum impedance for operation at 3 V. For an approximation of R_{OPT} and P_{OUT} at other supply voltages those two formulas can be used:

$$
R_{OPT} \sim V_S
$$

and

$$
P_{OUT} \sim R_{OPT}
$$

Power_output.wmf

Figure 3-9 $\;\;\;\;$ Output power P_o (mW) and collector efficiency E vs. load resistor R_L.

The DC collector current I_c of the power amplifier and the RF output power P_o vary with the load resistor $\mathsf{R}_{\mathsf{L}}.$ This is typical for overcritical operation of class C amplifiers. The collector current will show a characteristic dip at the resonance frequency for this type of "overcritical" operation. The depth of this dip will increase with higher values of $\mathsf{R}_\mathsf{L}.$

As [Figure 3-10](#page-30-0) shows, detuning beyond the bandwidth of the matching circuit results in an increase of the collector current of the power amplifier and in some loss of output power. This diagram shows the data for the circuit of the test board at the frequency of 434 MHz. The behaviour at 868 MHz is similar. The effective load resistance of this circuit is R_L = 700 Ω , which is the optimum impedance for operation at 3 V. This will lead to a dip of the collector current of approx. 40%.

pout_vs_frequ.wmf

Figure 3-10 Output power and collector current vs. frequency

C3, L2-C2 and C8 are the main matching components which are used to transform the 50 Ω load at the SMA-RF-connector to a higher impedance at the PA-output (700 Ω @ 3 V). L1 can be used for some finetuning of the resonant frequency but should not become too small in order to keep its losses low.

The transformed impedance of 700+j0 Ω at the PA-output-pin can be verified with a network analyzer using the following measurement procedure:

- 1. Calibrate your network analyzer.
- 2. Connect some short, low-loss 50 Ω cable to your network analyzer with an open end on one side. Semirigid cable works best.
- 3. Use the "Port Extension" feature of your network analyzer to shift the reference plane of your network analyzer to the open end of the cable.
- 4. Connect the center-conductor of the cable to the solder pad of the pin "PA" of the IC. The outer conductor has to be grounded. Very short connections have to be used. Do not remove the IC or any part of the matching-components!
- 5. Screw a 50 Ω dummy-load on the RF-I/O-SMA-connector
- 6. Be sure that your network analyzer is AC-coupled and turn on the power supply of the IC. The TDK5100 must not be in Transmit-Mode.
- 7. Measure the S-parameter S11

LoadImpedance50ohmBoard.wmf

Figure 3-11 S-parameters of the load at the PA-output

Above you can see the measurement of the evalboard with a span of 100 MHz. The evalboard has been optimized for 3 V. The load is about $700+10 \Omega$ at the transmit frequency.

A tuning-free realization requires a careful design of the components within the matching network. A simple linear CAE-tool will help to see the influence of tolerances of matching components.

Suppression of spurious harmonics may require some additional filtering within the antenna matching circuit. The total spectrum of a typical 50 Ω - Output testboard can be summarized as:

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4.1 Absolute Maximum Ratings

The AC / DC characteristic limits are not guaranteed. The maximum ratings must not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC may result.

Ambient Temperature under bias: T_A = -40°C to +125°C

Note: All voltages referred to ground (pins) unless stated otherwise.

Pins 5, 12 and 13 are grounded.

4.2 Operating Range

Within the operational range the IC operates as described in the circuit description.

4.3 AC/DC Characteristics

4.3.1 AC/DC Characteristics at 3V, 25°C

*) Derating linearly to a saturation voltage of max. 140 mV at $I_{CLKOUT} = 0$ mA

Ü) Power amplifier in overcritical C-operation Matching circuitry as used in the 50 Ohm-Output Testboard at the specified frequency. Tolerances of the passive elements not taken into account.

4.3.2 AC/DC Characteristics at 2.1 V ... 4.0 V, -40°C ... +125°C

*) The output-frequency range can be increased by limiting the temperature and supply voltage range.

Minimum f_{VCO} - 1 MHz => Minimum T_{amb} + 5°C

Maximum f_{VCO} + 1 MHz => Maximum T_{amb} - 5^oC

- Maximum f_{VCO} + 1 MHz => Minimum V_S + 25 mV, max. + 40 MHz.
- \uparrow) Derating linearly to a saturation voltage of max. 140 mV at $I_{\text{CI KOUT}} = 0$ mA
- á) Matching circuitry as used in the 50 Ohm-Output Testboard for 434 MHz operation. Tolerances of the passive elements not taken into account. Range @ 2.1 V, +25°C: 2.4 dBm +/- 0.7 dBm
- Typ. temperature dependency at 2.1 V: +0.4 dBm@-40°C and -1.4 dBm@+125°C, reference +25°C Range @ 3.0 V, +25°C: 5.0 dBm +/- 1.0 dBm
- Typ. temperature dependency at 3.0 V: +0.5 dBm@-40°C and -1.9 dBm@+125°C, reference +25°C Range @ 4.0 V, +25°C: 6.6 dBm +/- 2.0 dBm
- Typ. temperature dependency at 4.0 V: +0.6 dBm@-40°C and -3.1 dBm@+125°C, reference +25°C
- **) Matching circuitry as used in the 50 Ohm-Output Testboard for 868 MHz operation. Tolerances of the passive elements not taken into account. Range @ 2.1 V, +25°C: 0.0 dBm +/- 1.0 dBm
- Typ. temperature dependency at 2.1 V: +0.6 dBm@-40°C and -2.5 dBm@+125°C, reference +25°C Range @ 3.0 V, +25°C: 2.0 dBm +/- 2.0 dBm
- Typ. temperature dependency at 3.0 V: +0.9 dBm@-40°C and -3.6 dBm@+125°C, reference +25°C Range @ 4.0 V, +25°C: 3.2 dBm +/- 2.7 dBm
- Typ. temperature dependency at 4.0 V: +1.3 dBm@-40°C and -4.0 dBm@+125°C, reference +25°C

A smaller load impedance reduces the supply-voltage dependency.

A higher load impedance reduces the temperature dependency.